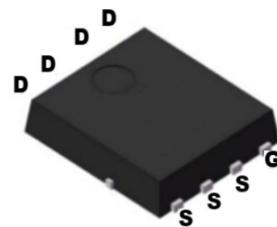




1. Features

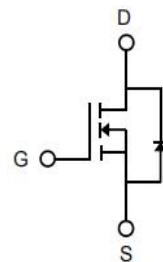
- V_{DS} 60V
- I_D (at $V_{GS}=10V$) 104A
- $R_{DS(ON)}$ (at $V_{GS}=10V$) 3.4mΩ(Typ)

PDFN5*6



2. Mechanical Data

- Case:Molded Plastic,PDFN5*6;
- Epoxy:UL 94V-0 rate flame retardant
- Terminals:Plated Leads Solderable per MIL-STD-750,Method-2026.
- Marking: marked on body.
- Mounting Position : Any.



- 1.Gate
2. Drain
3. Source

3. Absolute Maximum Ratings

Electrical Characteristics ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous ($T_C = 25^\circ C$)	I_D	104	A
Drain Current-Continuous($T_C = 100^\circ C$)		66	
Pulsed Drain Current	I_{DM}	391	A
Power Dissipation	P_D	78	W
Single Pulsed Avalanche energy ⁽¹⁾	E_{AS}	212	mJ
Junction Temperature	T_J	-55~+150	°C
Storage Temperature	T_{STG}	-55~+150	°C
Junction-to-Case Thermal Resistance	$R_{\theta JC}$	1.6	°C/W
Junction-to-Ambient Thermal Resistance	$R_{\theta JA}$	46	°C/W

**XNM104N06DF**

60V N-Channel SGT MOSFET

4.Electrical Characteristics

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	

Off Characteristics

Drain-source breakdown voltage	B_{VDSS}	$V_{GS} = 0V, I_D = 250\mu A$	60	-	-	V
Gate-source leakage current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$	-	-	1	μA
Gate threshold voltage	I_{GSS}	$V_{DS} = 0V, V_{GS} = 20V$	-	-	100	nA

On Characteristics

Drain-to-Source Leakage Current	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.2	1.7	2.5	V
Drain-to-Source On-Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 20A$	-	3.4	4.1	$m\Omega$
		$V_{GS} = 4.5V, I_D = 10A$	-	4.5	5.7	$m\Omega$

Dynamic Parameters

Gate Resistance	R_g	$f = 1 MHz$	-	1.5	-	Ω
Forward Transconductance	g_{fs}	$V_{DS} = 5 V, I_D = 20 A$	-	30	-	S
Input Capacitance	C_{iss}	$V_{DS} = 30V, V_{GS}=0V$ $f=1.0MHz$	-	1792	-	pF
Output Capacitance	C_{oss}		-	901	-	
Reverse Transfer Capacitance	C_{rss}		-	32	-	

Switching Parameters

Turn-on Delay Time	$t_{d(on)}$	$V_{DS}=30V, V_{GS}=10V, I_D=20A$ $R_G=3\Omega$	-	5.5	-	nS
Turn-on Rise Time	t_r		-	9.8	-	
Turn-off Delay Time	$t_{d(off)}$		-	26	-	
Turn-off Fall Time	t_f		-	16	-	
Total Gate Charge	Q_g	$V_{DS}=30V, I_D=20, V_{GS}=10V$	-	33	-	nC
Gate-Source Charge	Q_{gs}		-	5.6	-	
Gate-Drain Charge	Q_{gd}		-	7.3	-	

Drain-Source Diode Characteristics

Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS} = 0V, I_s = 2A$	-	0.7	1.2	V
------------------------------------	----------	-------------------------	---	-----	-----	---

Notes:

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. $V_{DD}=30V, V_{GS}=10V, L=0.5mH, I_{AS}=42A.$, Starting $TJ=25^\circ C$
3. The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
4. Essentially independent of operating temperature



5.Rating And Characteristic Curves

Fig. 1 On-Resistance vs. Gate-Source Voltage

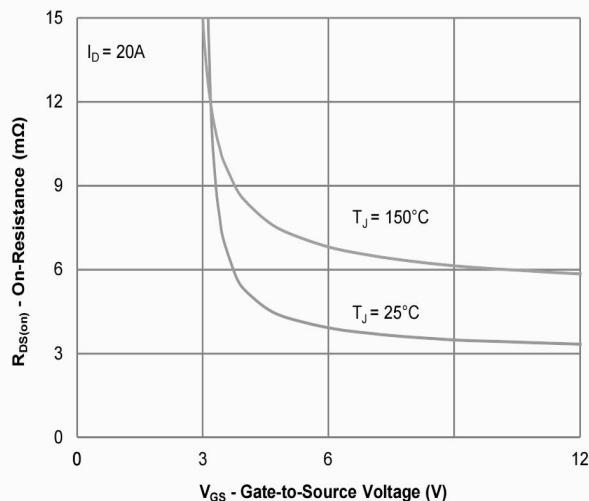


Fig 2 On-Resistance vs. Gate-Source Voltage

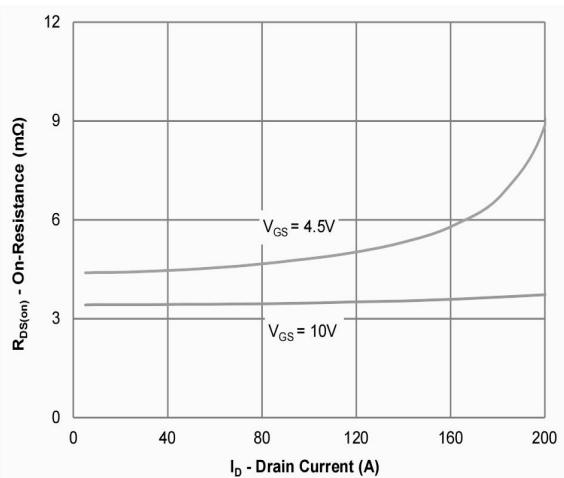


Fig.3 On-Resistance vs. Junction Temperature

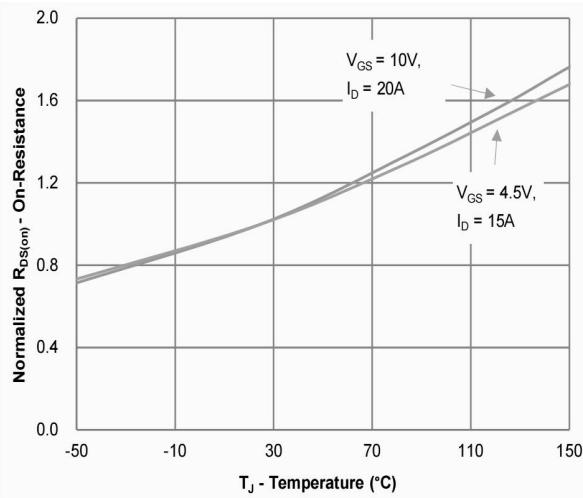


Fig.4 Source-Drain Diode Forward Voltage

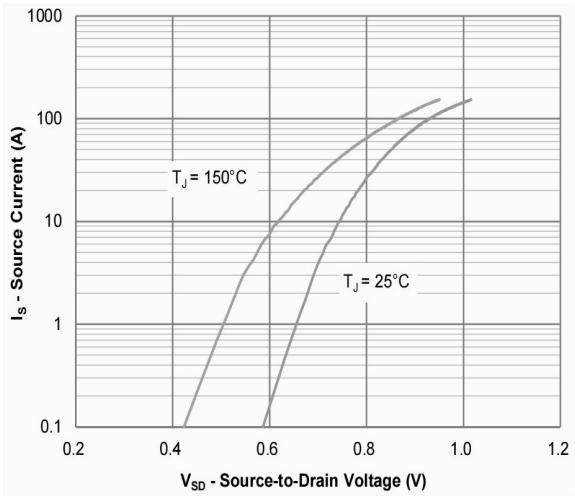


Fig.5 Gate Threshold Variation vs. Junction Temperature

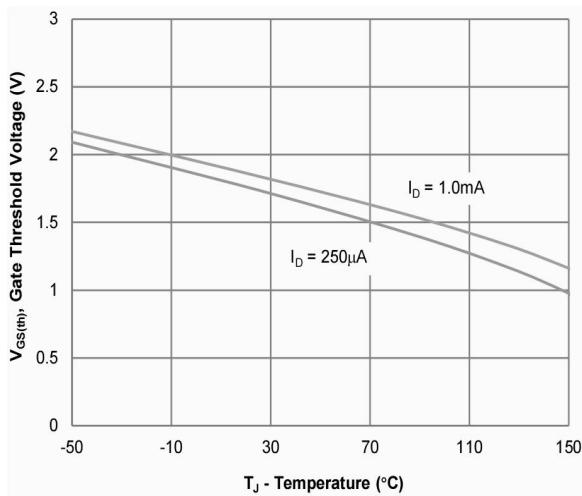
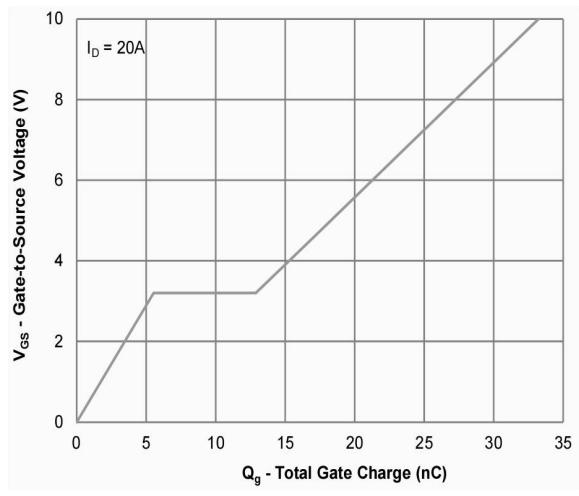


Fig.6 Gate Charge Characteristics



**XNM104N06DF**

60V N-Channel SGT MOSFET

Fig. 7 Capacitance Characteristics

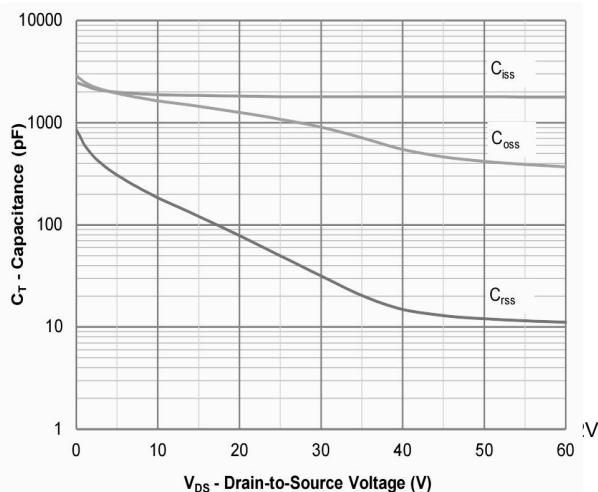


Fig 8 Power Derating

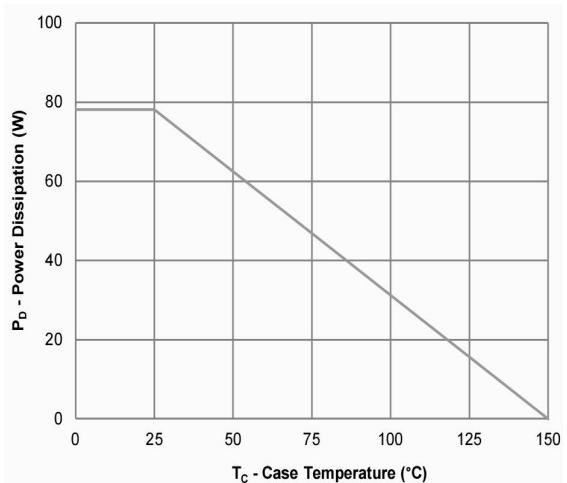


Fig.9 Current Derating

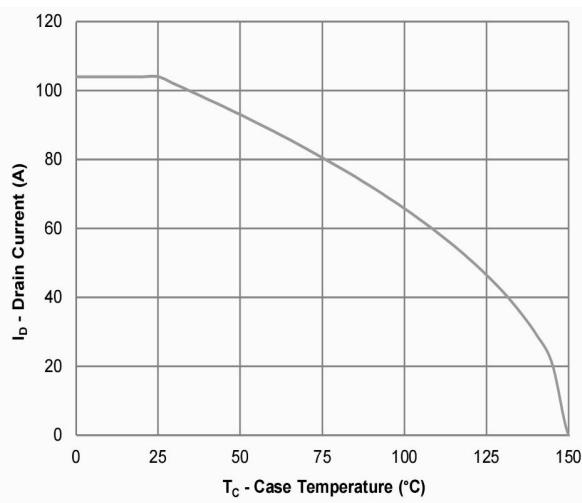


Fig.10 Safe Operating Area

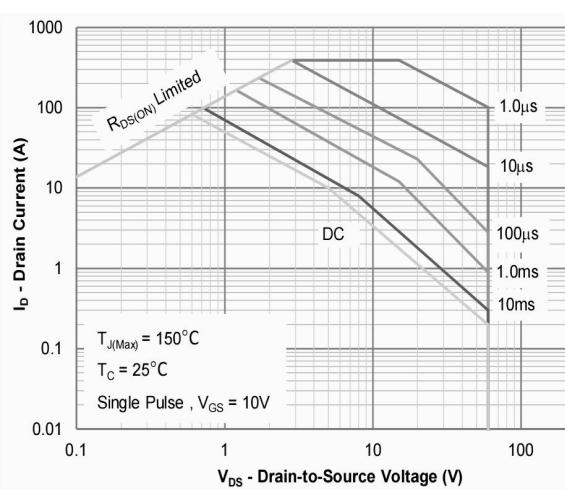
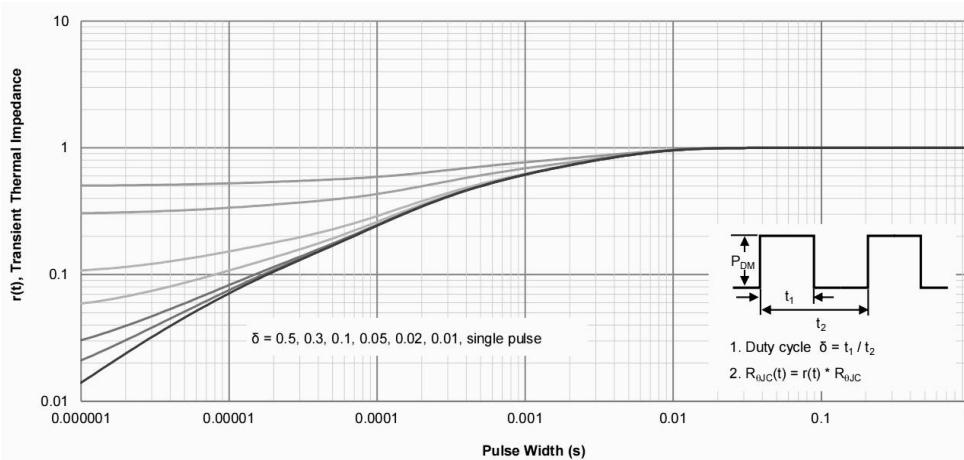
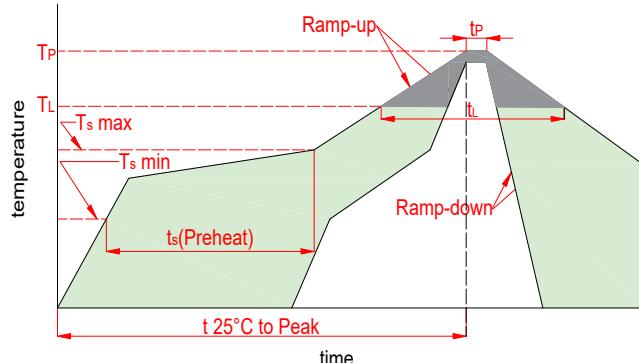


Fig.11 Normalized Maximum Transient Thermal Impedance



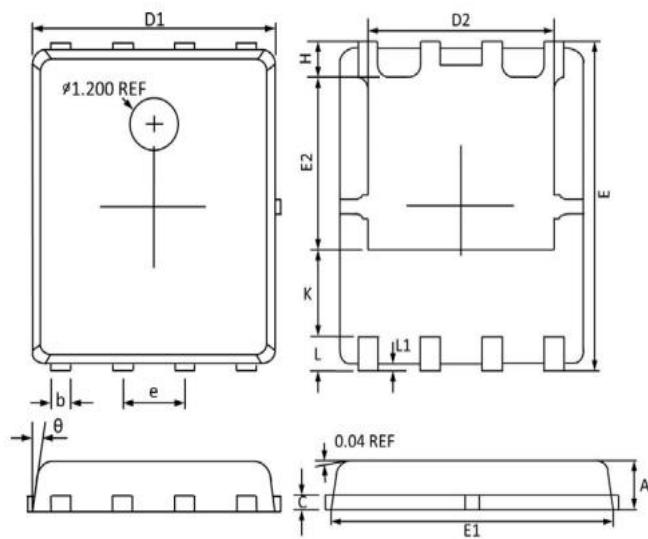


7. Soldering Parameters



Reflow Condition		Lead-free
Pre Heat	Temp. min(T_s (min))	150°C
	Temp. max(T_s (min))	200°C
	Time(min to max)(t_s)	60~180s
Aver. ramp up rate(Liquidus Temp.)(T_L)to peak		3°C/s max
T_s (max) to T_L -Ramp-up Rate		3°C/s max
Reflow	Temp.(T_L)(Liquidus)	217°C
	Temp.(t_L)(Liquidus)	60~150s
Peak Temp.(T_p)		260 ^{+0/-5} °C
Time within actual peak Temp.(t_p)		30s max
Ramp-down Rate		6°C/s max
Time 25°C to peak Tempe.(T_p)		8 minutes max
Do not exceed		260°C

8. Package Drawing



Dimensions	Inches		Millimeters	
	Min	Max	Min	Max
A	0.031	0.043	0.8	1.1
b	0.013	0.021	0.33	0.54
C	0.008	0.012	0.2	0.3
D1	0.189	0.201	4.8	5.1
D2	0.142	0.161	3.61	4.1
E	0.232	0.244	5.9	6.2
E1	0.224	0.232	5.7	5.9
E2	0.132	0.149	3.35	3.78
e	1.27BSC		1.27BSC	
H	0.016	0.028	0.41	0.7
K	0.043	0.059	1.1	1.5
L	0.020	0.028	0.51	0.71
L1	0.002	0.008	0.06	0.2

9. Package Information

Part Number	Package	Quantity(pcs)
XNM104N06DF	PDFN5*6	5000



Important Notice and Disclaimer

- Reproducing and modifying information of the document is prohibited without from XINNUO.
- XINNUO reserves the right to make changes to this document and its products and specifications.
- XINNUO disclaims any and all liability arising out of the application or use of any product including damages incidentally and consequentially occurred.
- XINNUO does not assume any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.
- Applications shown on the here in document are examples of standard use and operation. Customers are responsible in comprehending the suitable use in particular applications.XINNUO makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.
- The products shown her are not designed and authorized for equipments requiring high level of reliability or relating to human life and for any applications concerning life-saving or life-sustaining, such as medical instruments, transportation equipment, aerospace machinery et cetera. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify XINNUO for any damages resulting from such improper use or sale.
- Since XINNUO uses lot number as the tracking base, please provide the lot number for tracking when complaining.